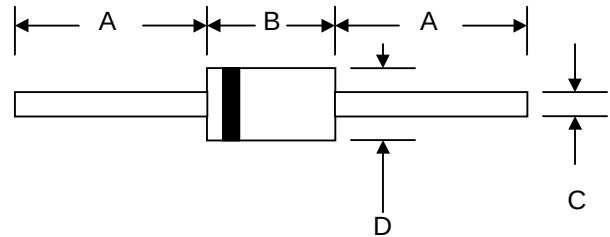


SILICON BIDIRECTIONAL DIACS
Features

- VBO:28-36V
- Low Breakover Current


Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.35 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- **Lead Free: For RoHS / Lead Free Version,**

DO-41		
Dim	Min	Max
A	25.4	—
B	4.06	5.21
C	0.70	0.90
D	2.00	2.72
All Dimensions in mm		

DO-35		
Dim	Min	Max
A	27.5	—
B	—	3.8
C	0.50	0.60
D	—	2.0
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ $T_A=25^\circ\text{C}$
ABSOLUTE RATINGS

PARAMETERS	SYMBOL	VALUE		UNITS
		DB3		
Power Dissipation on Printed Circuit(L=10mm) $T_A=50^\circ\text{C}$	P_c	150		mW
Repetitive Peak on-state Current $T_p=10\mu\text{S}$ $f=100\text{Hz}$	I_{TRM}	2.0		A
Storage and Operating Junction Temperature	T_{STG}/T_J	-40 to +125		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS

PARAMETERS	SYMBOLS	TEST CONDITIONS	VALUE		UNITS
			DB3		
Breakover Voltage*	V_{BO}	C=22nF** See Diagram 1	Min	28	V
			Typ	32	
			Max	36	
Breakover Voltage Symmetry	$1+V_{BO1}$ $1-V_{BO1}$	C=22nF** See Diagram 1	Max	± 3	V
Dynamic Breakover Voltage	$1 \pm \Delta V_1$	$\Delta I = (I_{BO} \text{ to } I_F = 10\text{mA})$ See FIG 1	Min	5	V
Output Voltage*	V_o	See FIG 2	Min	5	V
Breakover Current*	I_{BO}	C=22nF**	Max	100	μA
Rise Time*	t_r	See FIG 3	Typ	1.5	μS
Leakage Current*	I_B	$I_B = 0.5 V_{BO} \text{ MAX}$ See FIG 3	Max	10	μA

NOTE:* Electrical characteristics applicable in both forward and reverse directions.

** Connected in parallel with the devices.

FIG.1-CURRENT-VOLTAGE CHARACTERISTICS

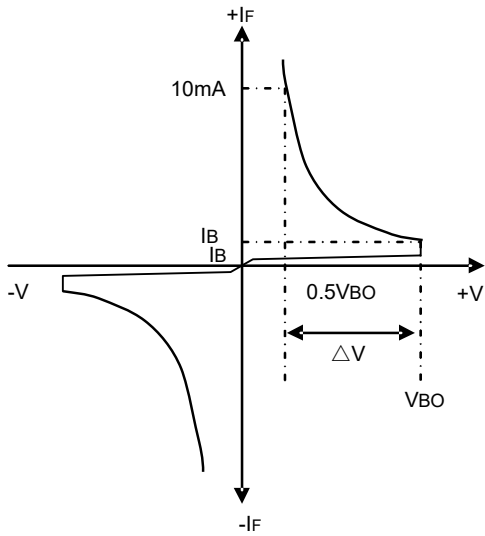


FIG.2-TEST CIRCUIT FOR OUTPUT VOLTAGE

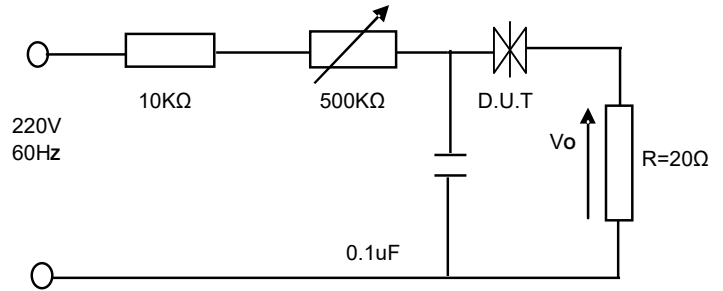


FIG.3-TEST CIRCUIT SEE FIG.2 ADJUST R FOR $I_p=0.5A$

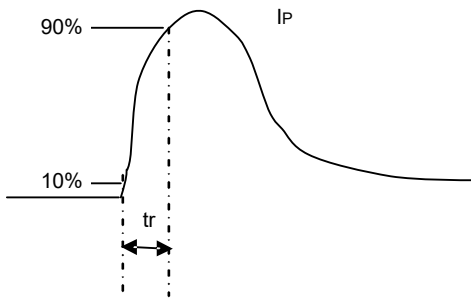


FIG.4-TEST CIRCUIT FOR OUTPUT VOLTAGE

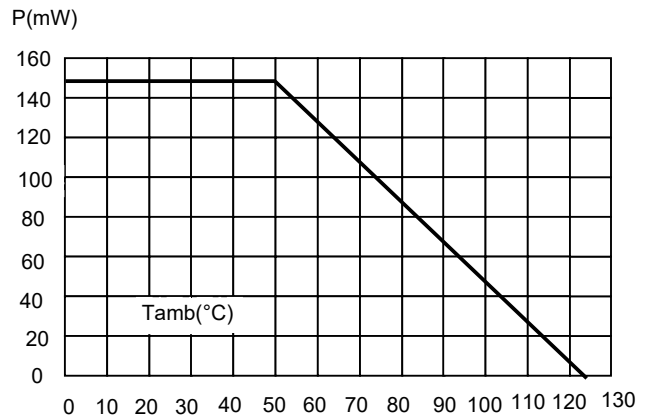


FIG.5-RELATIVE VARIATION OF VBO VERSUS JUNCTION TEMPERATURE(TYPICAL VALUES)

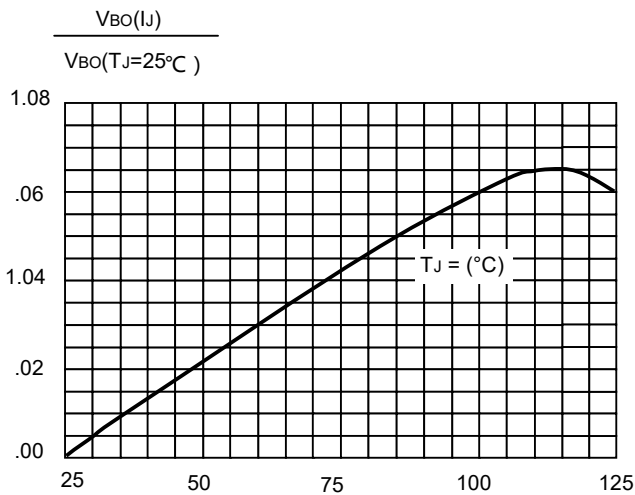


FIG.6-PEAK PULSE CURRENT VERSUS PULSE DURATION (MAXIMUM VALUES)

